



Solid State Devices, Inc.

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DESIGNER'S DATA SHEET

Part Number / Ordering Information ^{1/}

SFT501 — —
 SFT503 — —
 — Screening ^{2/} — = Not Screen
 TX = TX Level
 TXV = TXV Level
 S = S Level
 — Package ^{3/} — = TO-5

SFT501 and SFT503 Series

5 AMP 200 Volts HIGH SPEED PNP Transistor

Features:

- Radiation Tolerant
- Fast Switching
- High Frequency, 50 MHz Typical
- BVCEO 150 Volts Min
- High Linear Gain
- Very Low Leakage and Saturation
- 200°C Operating Temperature
- Gold Eutectic Die Attach
- Designed for Complementary Use with SFT502 and SFT504

Maximum Ratings	Symbol	Value	Units
Collector – Emitter Voltage	V _{CEO}	150	Volts
Collector – Base Voltage	V _{CBO}	200	Volts
Emitter – Base Voltage	V _{EBO}	7	Volts
Continues Collector Current	I _C	5	Amps
Base Current	I _B	1	Amps
Power Dissipation @ TC = 50°C Derate above 50°C	P _D	10 66.6	W mW/°C
Operating & Storage Temperature	Top & Tstg	-65 to +200	°C
Maximum Thermal Resistance Junction to Case	R _{θJC}	22	°C/W

NOTES:

* Pulse Test: Pulse Width = 300μsec, Duty Cycle = 2%

^{1/} For Ordering Information, Price, and Availability Contact Factory.

^{2/} Screening per MIL-PRF-19500

^{3/} For Package Outlines Contact Factory.

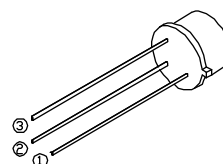
^{4/} Unless Otherwise Specified, All Electrical Characteristics @25°C.

Available parts:

SFT501

SFT503

TO-5



PIN ASSIGNMENT

Package	Pin 1	Pin 2	Pin 3 (Case)
TO-5	Emitter	Base	Collector

NOTE: All specifications are subject to change without notification.
 SCD's for these devices should be reviewed by SSDI prior to release.

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DATA SHEET #: TR0040D

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SFT501 and SFT503 Series

Electrical Characteristic ^{4/}		Symbol	Min	Typ	Max	Units
Collector – Emitter Breakdown Voltage	$I_C = 50\text{mA}$	BV_{CEO}	150	200	—	Volts
Collector – Base Breakdown Voltage	$I_C = 200\mu\text{A}$	BV_{CBO}	200	275	—	Volts
Emitter – Base Breakdown Voltage	$I_E = 200\mu\text{A}$	BV_{EBO}	7	13	—	Volts
Collector – Cutoff Current	$V_{CE} = 100\text{ V}$	I_{CEO}	—	—	1.0	μA
Collector – Cutoff Current	$V_{CB} = 100\text{ V}$	I_{CBO}	—	—	500	nA
Emitter – Cutoff Current	$V_{EB} = 6\text{ V}$	I_{EBO}	—	—	500	nA
DC Current Gain *						
SFT501	$V_{CE} = 5\text{ V}, I_C = 50\text{mA}$	h_{FE}	20	—	—	—
	$V_{CE} = 5\text{ V}, I_C = 2.5\text{ A}$		30	—	—	
	$V_{CE} = 5\text{ V}, I_C = 5\text{ A}$		20	70	—	
SFT503	$V_{CE} = 5\text{ V}, I_C = 50\text{mA}$		50	—	—	
	$V_{CE} = 5\text{ V}, I_C = 2.5\text{ A}$		50	—	—	
	$V_{CE} = 5\text{ V}, I_C = 5\text{ A}$		40	70	—	
Collector – Emitter Saturation Voltage *	$I_C = 2.5\text{A}, I_B = 250\text{mA}$ $I_C = 5.0\text{A}, I_B = 500\text{mA}$	$V_{CE(Sat)}$	— —	0.35 0.6	0.75 1.5	Volts
Base – Emitter Saturation Voltage *	$I_C = 2.5\text{A}, I_B = 250\text{mA}$ $I_C = 5.0\text{A}, I_B = 500\text{mA}$	$V_{BE(Sat)}$	— —	1.0 1.2	1.3 1.5	Volts
Current Gain Bandwidth Product	$V_{CE} = 5\text{V}, I_C = 0.5\text{A}, f = 10\text{MHz}$	f_T	40	60	—	MHz
Output Capacitance	$V_{CB} = 10\text{V}, I_E = 0\text{A}, f = 1\text{MHz}$	C_{ob}	—	130	225	pF
Input Capacitance	$V_{BE} = 10\text{V}, I_C = 0\text{A}, f = 1\text{MHz}$	C_{ib}	—	450	600	pF
Delay Time	$V_{CC} = 50\text{V},$ $I_C = 5\text{A},$ $I_{B1} = I_{B2} = 0.5\text{A}$	t_d	—	25	50	nsec
Rise Time		t_r	—	40	250	nsec
Storage Time		t_s	—	320	600	nsec
Fall Time		t_f	—	130	300	nsec

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